AP30N06BD

60V N-Channel Enhancement Mode MOSFET

Description

The AP30N06BD uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

V_{DS} = 60V I_D =30A

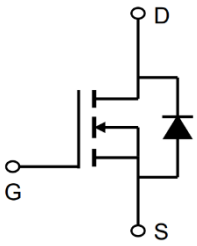
$R_{DS(ON)}$ <36mΩ @ V_{GS}=10V **（Type：28mΩ）**

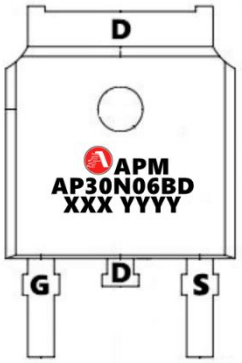
Application

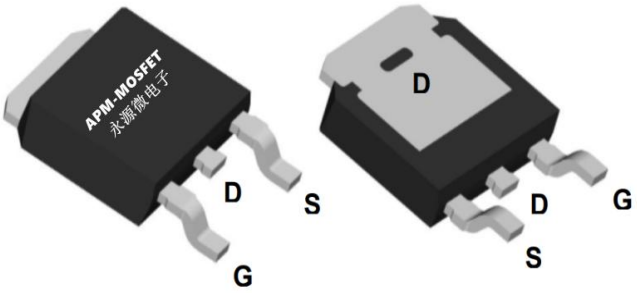
LED lamp

Load switch

Uninterruptible power supply







Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP30N06BD	TO252-3L	AP30N06BD XXX YYYY	2500

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Value	Unit
VDSS	Drain-Source Voltage	60	V
VGSS	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	30	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	17	A
IDM	Pulsed Drain Current	74	A
IAS	Avalanche Current	13	A
EAS	Single Pulsed Avalanche Energy	22	mJ
P_D@T_C=25℃	Power Dissipation	31.3	W
TJ, TSTG	Operating and Storage Temperature Range	-55 to +175	℃
R_{θ}JA	Thermal Resistance Junction-Ambient [1]	62	℃/W
R_{θ}JC	Thermal Resistance Junction-Case[1]	4	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	65	---	V
△BVDSS/△TJ	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.044	---	V/℃
RDS(ON)	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=15A	---	28	36	mΩ
		V_{GS}=4.5V , I_D=7A	---	38	45	mΩ
VGS(th)	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.6	2.5	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.8	---	mV/℃
IDSS	Drain-Source Leakage Current	V_{DS}=48V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=48V , V_{GS}=0V , T_J=55℃	---	---	5	
IGSS	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=15A	---	25.3	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.5	---	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=48V , V_{GS}=10V , I_D=15A	---	19	---	nC
Q_{gs}	Gate-Source Charge		---	2.5	---	
Q_{gd}	Gate-Drain Charge		---	5	---	
Td(on)	Turn-On Delay Time	V_{DD}=30V , V_{GS}=10V , R_G=3.3Ω I_D=15A	---	2.8	---	ns
T_r	Rise Time		---	16.6	---	
Td(off)	Turn-Off Delay Time		---	21.2	---	
T_f	Fall Time		---	5.6	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	1027	---	pF
Coss	Output Capacitance		---	65	---	
Crss	Reverse Transfer Capacitance		---	46	---	
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	20	A
ISM	Pulsed Source Current[2,6]		---	---	40	A
VSD	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=15A , dI/dt=100A/μs , T_J=25℃	---	12.2	---	nS
Q_{rr}	Reverse Recovery Charge		---	7.3	---	nC

Note :

1、The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width .The EAS data shows Max. rating .

3、The test cond≦ 300us duty cycle ≦ 2%, duty cycle ition is TJ =25℃, VDD =48V, VG =10V, RG =25Ω, L=0.1mH, IAS =13A

4、The power dissipation is limited by 175℃ junction temperature

5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

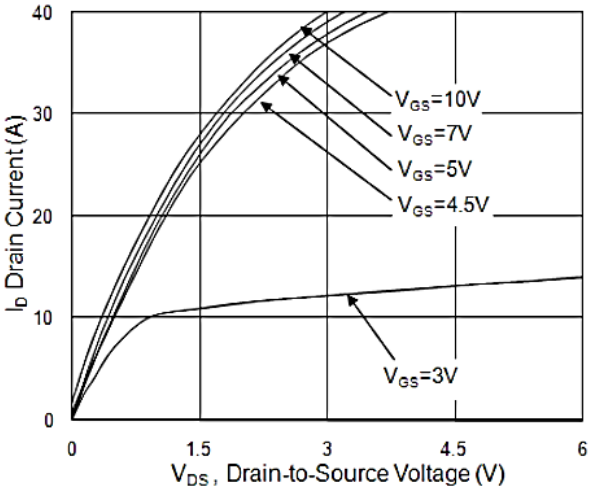


Fig.1 Typical Output Characteristics

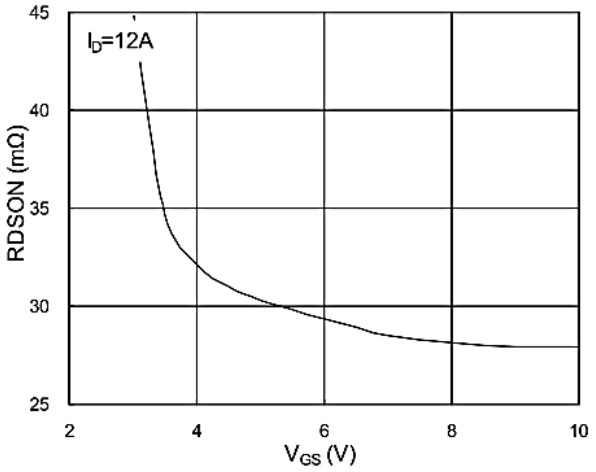


Fig.2 On-Resistance vs. Gate-Source

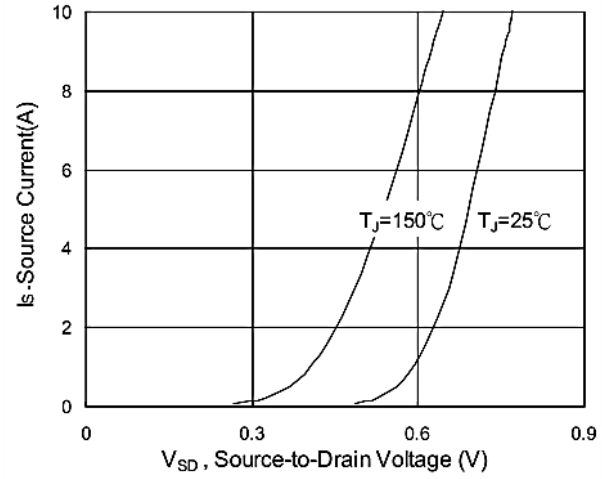


Fig.3 Forward Characteristics Of Reverse

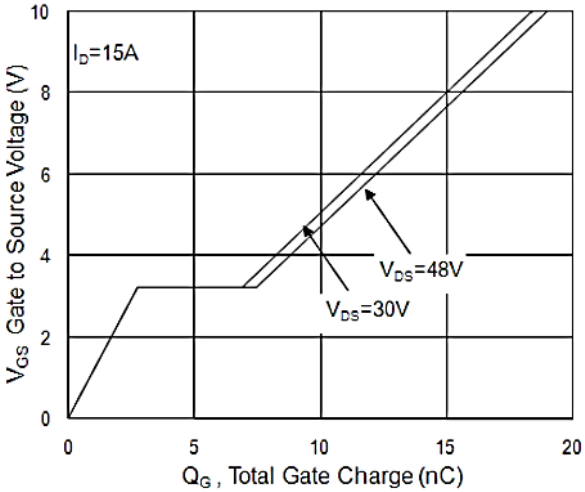


Fig.4 Gate-Charge Characteristics

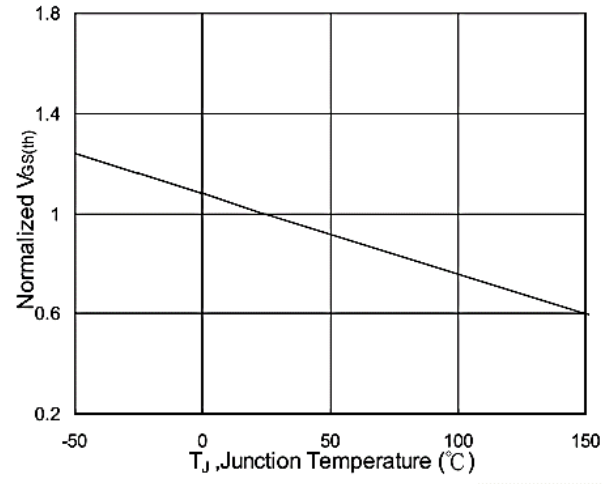


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

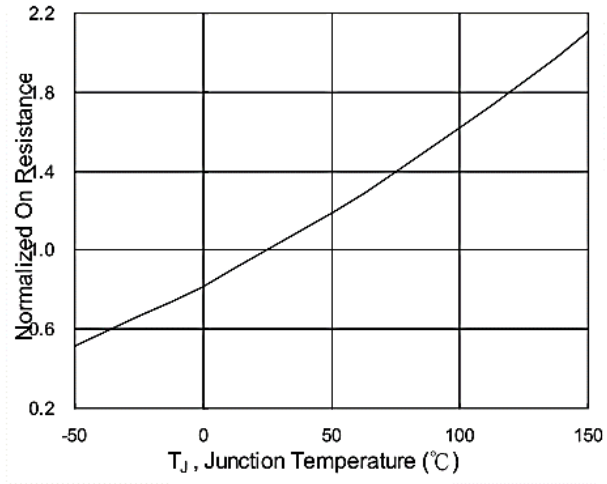


Fig.6 Normalized R_{DSON} vs. T_J

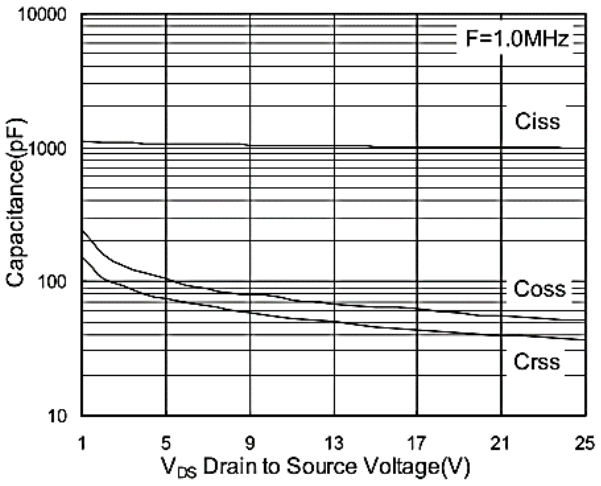


Fig.7 Capacitance

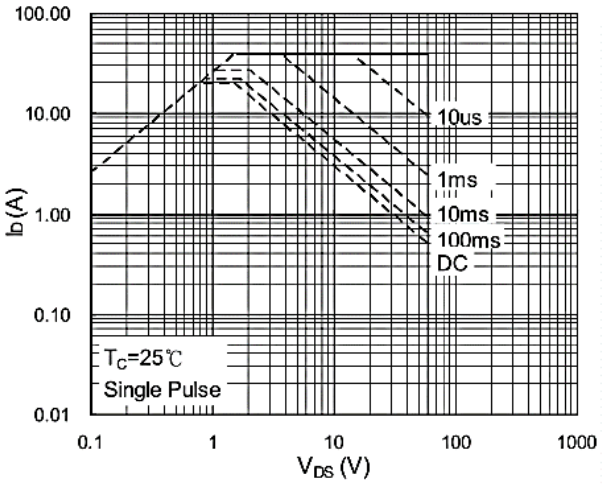


Fig.8 Safe Operating Area

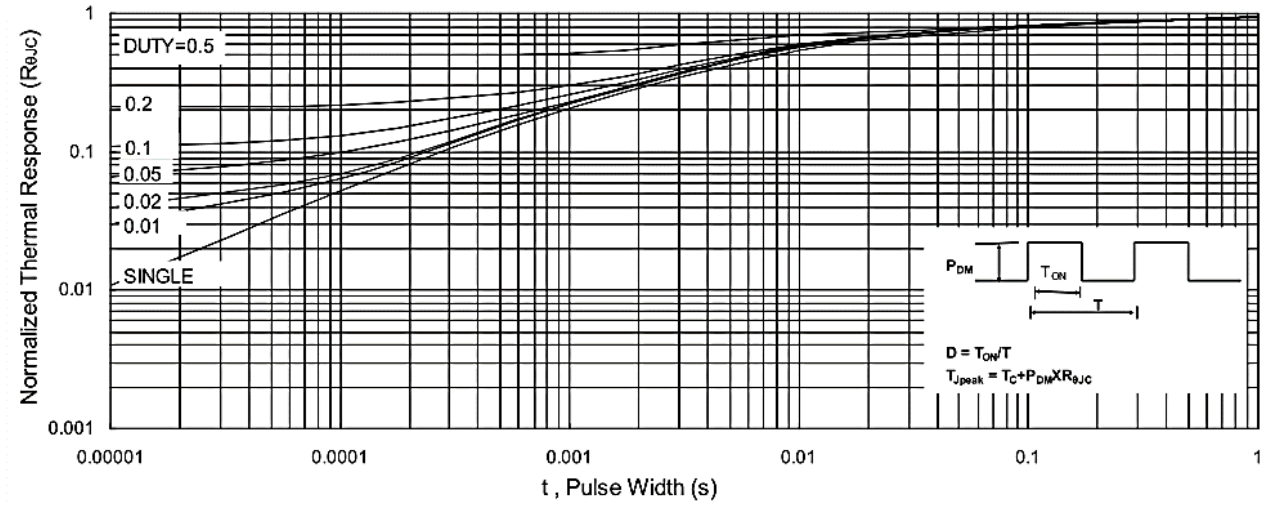


Fig.9 Normalized Maximum Transient Thermal Impedance

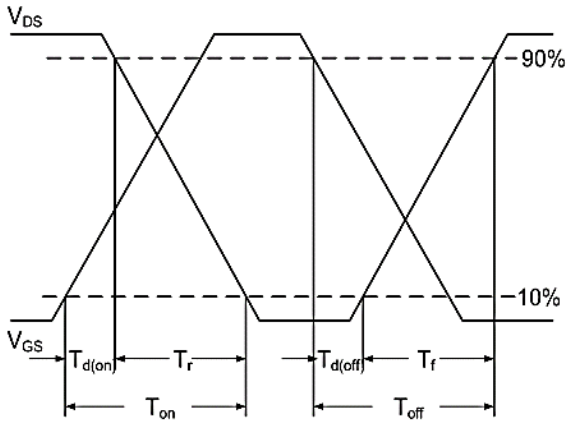


Fig.10 Switching Time Waveform

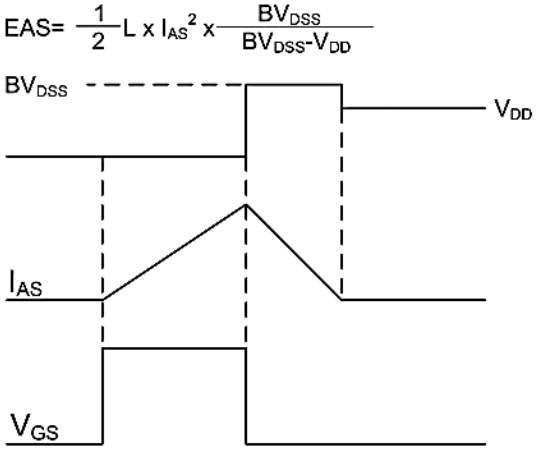
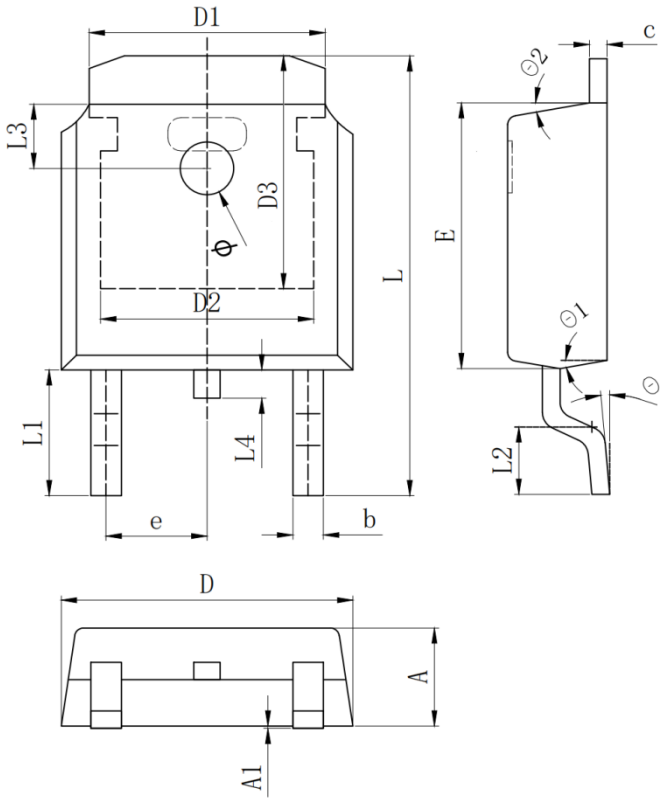


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data-TO252-3L



Symbol	Dimensions In Millimeters		
	min.	typ.	max.
A	2.10	2.30	2.50
A1	0.00	0.064	0.128
b	0.64	0.75	0.86
c	0.45	0.52	0.60
D	6.40	6.60	6.80
D1	5.33REF		
D2	4.83REF		
D3	5.25REF		
E	5.90	6.10	6.30
e	2.286TYP		
L	9.80	10.10	10.40
L1	2.888REF		
L2	1.40	1.50	1.70
L3	1.65REF		
L4	0.60	0.80	1.00
ϕ	1.10	1.20	1.30
θ	0°		10°
θ1	5°		10°
θ2	5°		10°

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60V N-Channel Enhancement Mode MOSFET

Edition	Date	Change
REV1.0	2023/1/23	Initial release
REV1.1	2026/6/24	Update LOGO And Corrected Manual POD

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